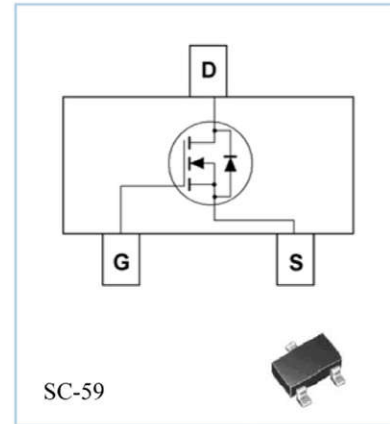


## N-Channel Enhancement Mode MOSFET Feature

- 30V/4.2A,  $R_{DS(ON)} = 65\text{m}\Omega$  (MAX) @ $V_{GS} = 10\text{V}$ .  
 $R_{DS(ON)} = 70\text{m}\Omega$  (MAX) @ $V_{GS} = 4.5\text{V}$ .
- Super High dense cell design for extremely low  $R_{DS(ON)}$ .
- Reliable and Rugged.
- SC-59 for Surface Mount Package.



## Applications

- Power Management  
Portable Equipment and Battery Powered Systems.

## Absolute Maximum Ratings

$T_A=25^\circ\text{C}$  Unless Otherwise noted

Parameter	Symbol	Limit	Units
Drain-Source Voltage	$V_{DS}$	30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous	$I_D$	4.2	A

## Electrical Characteristics

$T_A=25^\circ\text{C}$  Unless Otherwise noted

Parameter	Symbol	Test Conditions	Min	Typ.	Max	Units
<b>Off Characteristics</b>						
Drain to Source Breakdown Voltage	BVDSS	$V_{GS}=0\text{V}, I_D=250\mu\text{A}$	30	-	-	V
Zero-Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=24\text{V}, V_{GS}=0\text{V}$	-	-	1	$\mu\text{A}$
Gate Body Leakage Current, Forward	$I_{GSSF}$	$V_{GS}=20\text{V}, V_{DS}=0\text{V}$	-	-	100	nA
Gate Body Leakage Current, Reverse	$I_{GSSR}$	$V_{GS}=-20\text{V}, V_{DS}=0\text{V}$	-	-	-100	nA
<b>On Characteristics</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}, I_D=250\mu\text{A}$	0.6	-	1.5	V
Static Drain-source On-Resistance	$R_{DS(ON)}$	$V_{GS}=10\text{V}, I_D=3.5\text{A}$	-	55	65	$\text{m}\Omega$
		$V_{GS}=4.5\text{V}, I_D=2\text{A}$	-	60	70	$\text{m}\Omega$
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
Drain-Source Diode Forward Voltage	VSD	$V_{GS}=0\text{V}, I_S=1.25\text{A}$			1.2	V